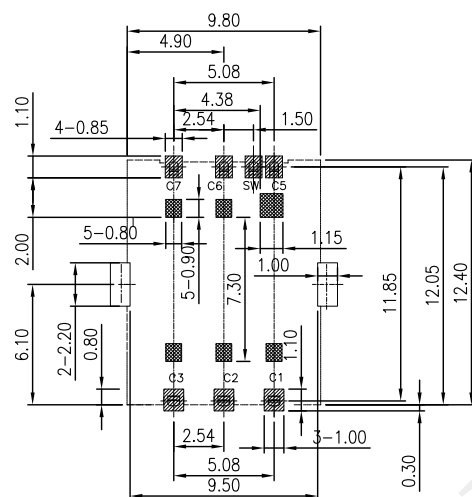
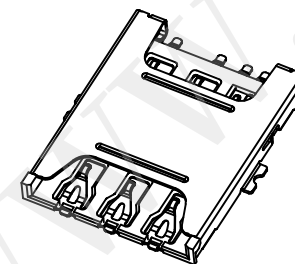
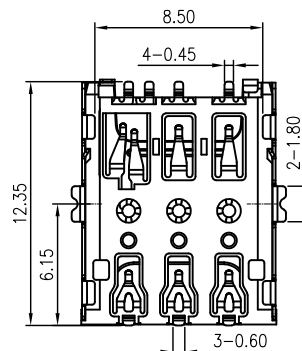
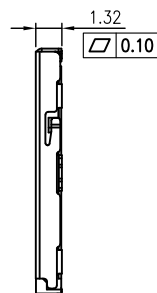
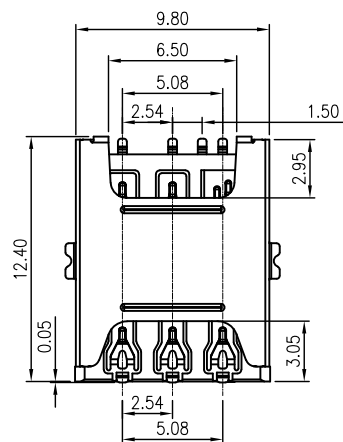
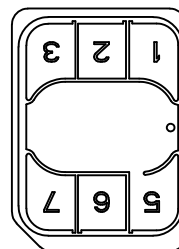




Nano SIM Circuit Description:

PIN No.	FUNCTION
C1	VCC
C2	RST
C3	CLK
C5	GND
C6	VPP
C7	I/O

RECOMMENDED P.C.B LAYOUT COMPONENT SIDE(TOLERANCE ± 0.05)

TECHNICAL CHARACTERISTICS1.

1.General Characteristics

Dimensions:12.40X9.80WX1.35H mm

Weight: Approx 0.50 $\pm$ 0.2g

Durability:1,500cycles min.

2.Electrical Characteristics

Contact resistance:50m Ω typical,
100m. maxInsulation resistance:>1000M Ω /500V DC

Solderability

Vaporphase:215 $^{\circ}$ C,30sec.MaxIRreflow:250C,5sec.MaxManual soldering:370 $^{\circ}$ C,3sec.Max

4.Environmental Characteristics

Operating temperature:-40 $^{\circ}$ C~+85 $^{\circ}$ C

Operating humidity:10%~+95%RH

3	CONTACT	1	COPPER ALLOY	CONTACT AREA:GOLD PLATED
2	SHELL	1	STAINLESS STEEL	
1	HOUSING	1	LCP UL94V-0	COLOR:BLACK
NO.	DESCRIPTION	Q'TY	Material	Finish



深圳市华宇创精密电子有限公司

TOLERANCE: X.X ± 0.30 X.XX ± 0.25 X.XXX ± 0.15 X." ± 2 " X.X" ± 0.5 "	DRAWN BY : 陈一鸣	DATE : 2014-02-23	PART NAME: NANO SIM 6P 1.32H 带检测P 脚向外
	CHECKED BY: 马跃	DATE : 2014-02-23	PART NO. HYC384-SIM07-132
	APPROVED BY: 邱敏	DATE : 2014-02-23	MOLD NO.
UNIT: mm [inch] SCALE:1:1 SIZE: A4			DRAW NO: HYC-2602281018
			SHEET NO. 1 OF 1